



Description

The NTR3C21NZT1G uses advanced trench technology

to provide excellent $R_{DS(ON)}$, low gate charge and

operation with gate voltages as low as 2.5V. This

device is suitable for use as a Battery protection

or in other Switching application.

General Features

$V_{DS} = 20V$ $I_D = 6.5A$

$R_{DS(ON)} < 22m\Omega$ @ $V_{GS} = 4.5V$

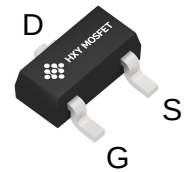
ESD=2500HBM

Application

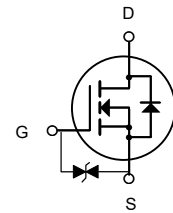
Battery protection

Load switch

Uninterruptible power supply



SOT-23-3L
(SOT-23-3)



N-Channel MOSFET

Ordering Information

Product ID	Pack	Marking	Qty(PCS)
NTR3C21NZT1G	SOT-23-3L(SOT-23-3)	AGBV 1N	3000

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Drain Current-Continuous	6.5	A
I_{DM}	Drain Current-Pulsed (Note 1)	30	A
P_D	Maximum Power Dissipation	1.4	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 2)	89	$^\circ C/W$



Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20		-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$	-	-	± 10	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.45	0.7	1.0	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=6.5A$	-	14	22	m Ω
		$V_{GS}=2.5V, I_D=5.5A$	-	17	26	m Ω
		$V_{GS}=1.8V, I_D=5A$	-	28	40	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=6.5A$	8	-	-	S
Input Capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0V,$ $F=1.0MHz$	-	660	-	PF
Output Capacitance	C_{oss}		-	160	-	PF
Reverse Transfer Capacitance	C_{rss}		-	87	-	PF
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, R_L=1.5\Omega$ $V_{GS}=5V, R_{GEN}=3\Omega$	-	0.5		nS
Turn-on Rise Time	t_r		-	1		nS
Turn-Off Delay Time	$t_{d(off)}$		-	12		nS
Turn-Off Fall Time	t_f		-	4		nS
Total Gate Charge	Q_g	$V_{DS}=10V, I_D=6.5A,$ $V_{GS}=4.5V$	-	8		nC
Gate-Source Charge	Q_{gs}		-	2.5	-	nC
Gate-Drain Charge	Q_{gd}		-	3	-	nC
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=6.5A$	-	-	1.2	V
Diode Forward Current ^(Note 2)	I_S		-	-	6.5	A

Notes:

Repetitive Rating: Pulse width limited by maximum junction temperature. Surface Mounted on FR4 Board, $t \leq 10$ sec.
Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
Guaranteed by design, not subject to production



Typical Characteristics

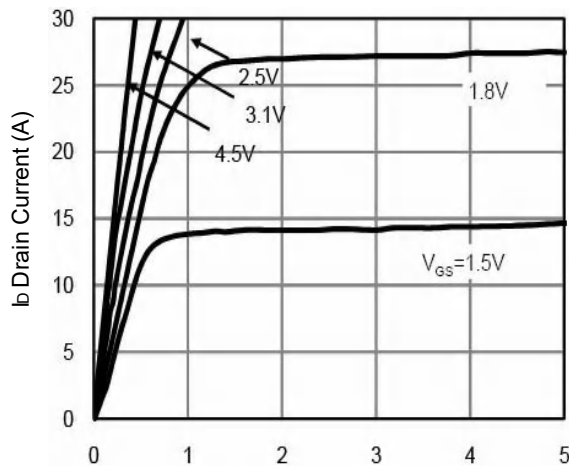


Fig.1 Typical Output Characteristics

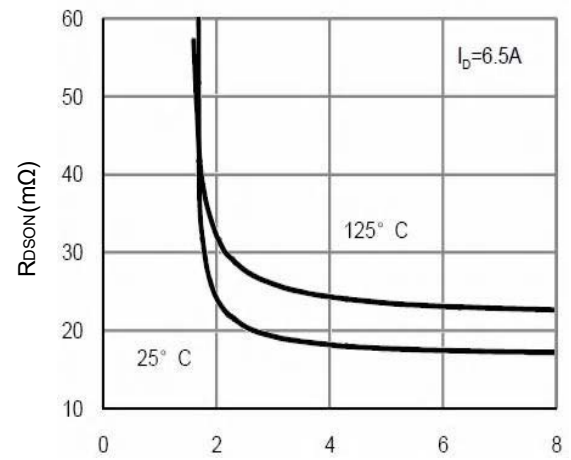


Fig.2 On-Resistance vs. Gate-Source

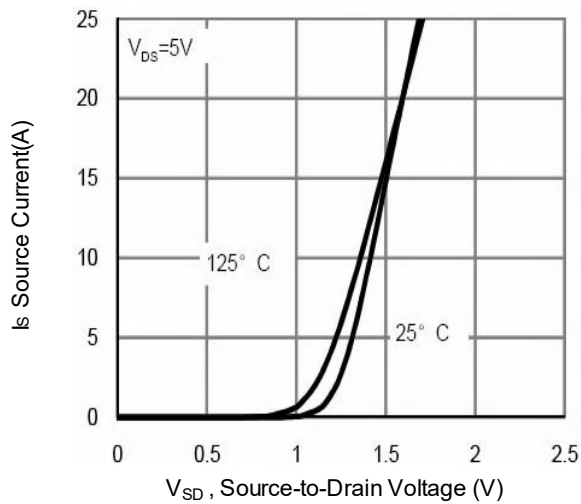


Fig.3 Forward Characteristics of Reverse

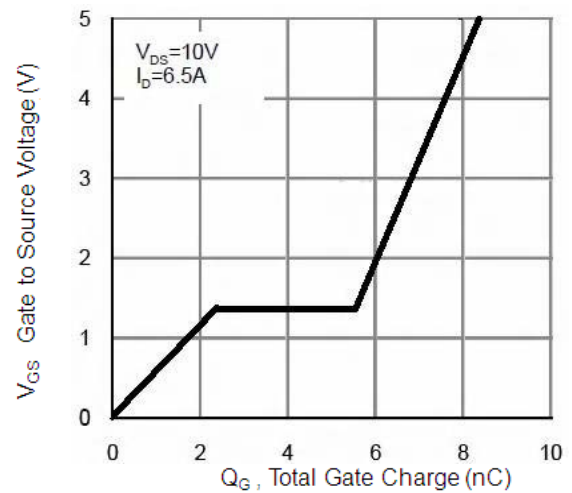


Fig.4 Gate-Charge Characteristics

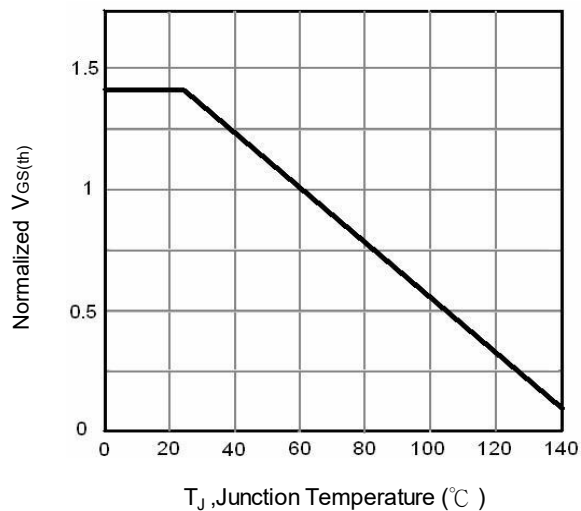


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

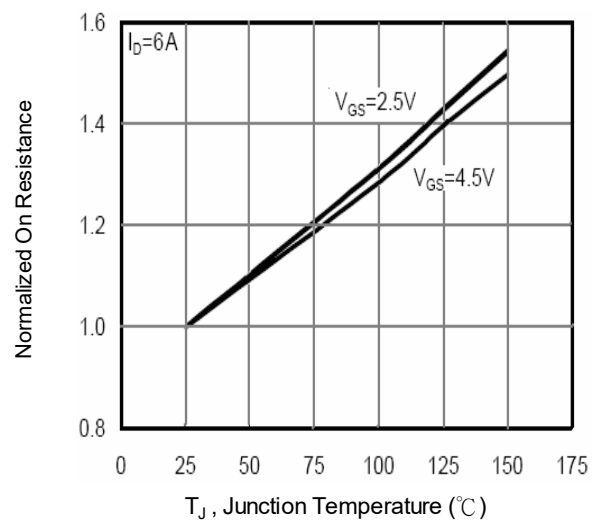
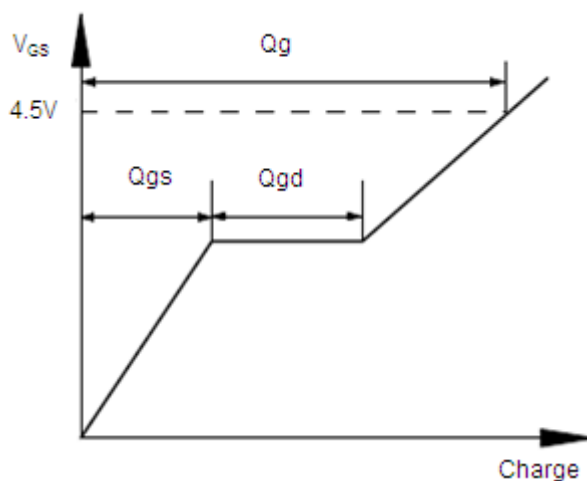
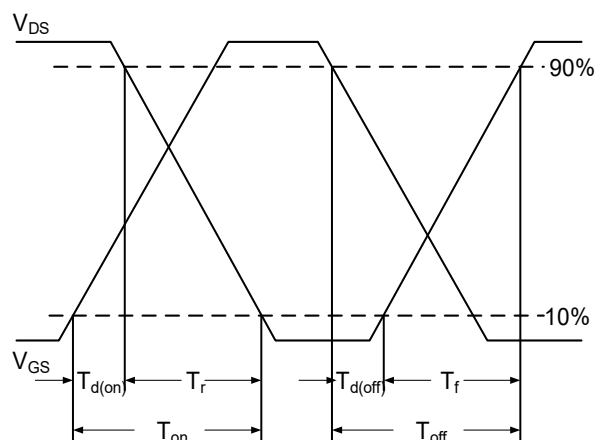
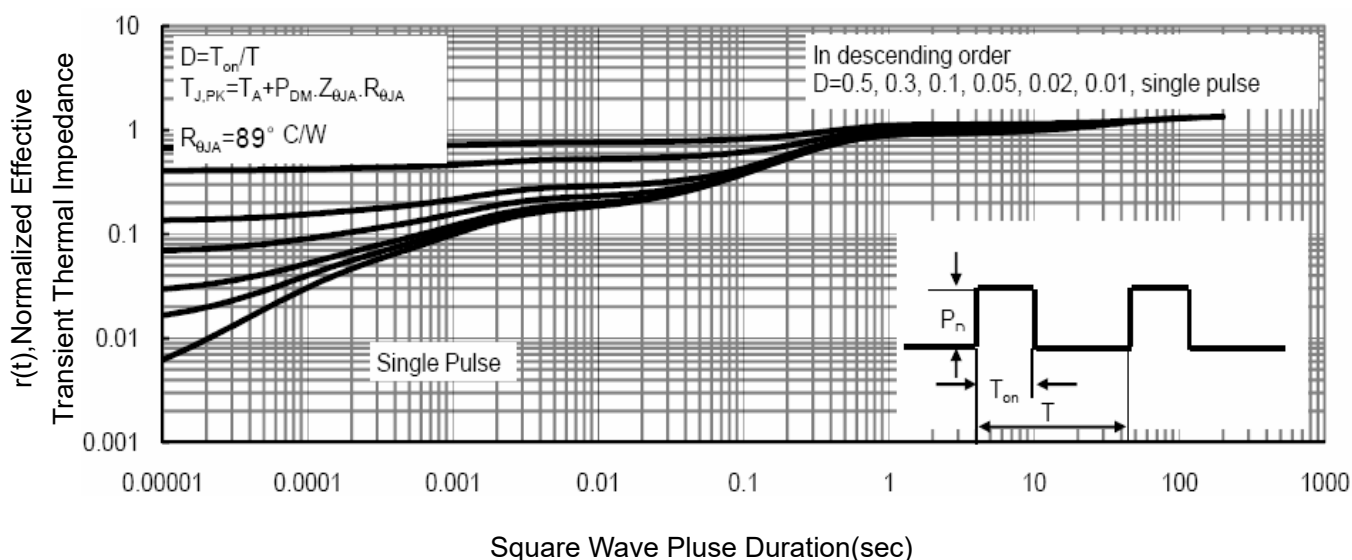
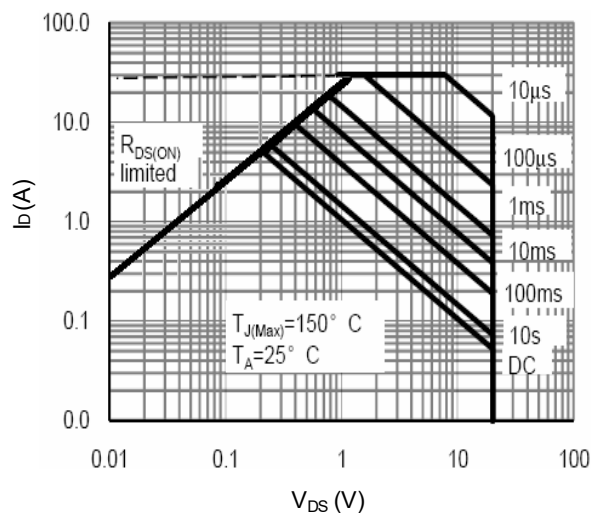
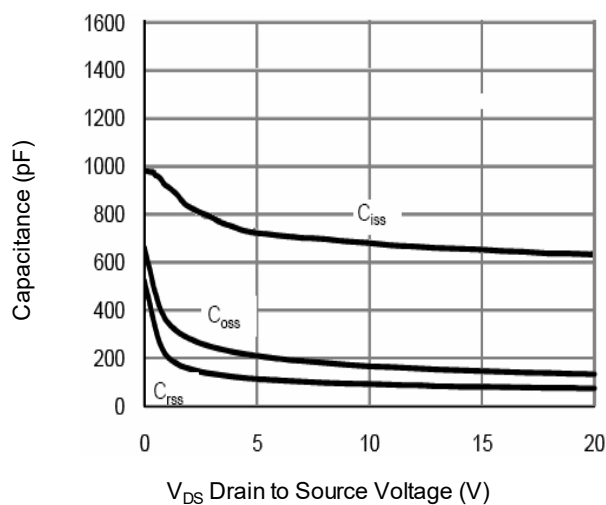


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

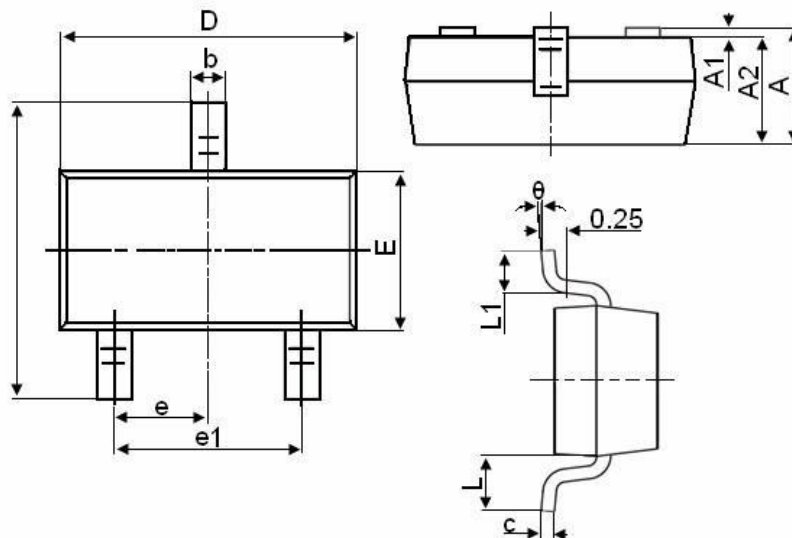


N-Channel Enhancement Mode MOSFET





SOT-23-3L(SOT-23-3) Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.300	0.500
c	0.100	0.200
D	2.800	3.000
E	1.500	1.700
E1	2.650	2.950
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.600
θ	0°	8°



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